

AMENDMENTS TO THE SPECIFICATION

Please amend the title in all instances as follows:

BIPOLAR TRANSISTOR WITH AN ULTRA SMALL SELF-ALIGNED POLYSILICON
EMITTER AND METHOD OF FORMING THE SILICON GERMANIUM BASE OF THE
TRANSISTOR

Please amend the first paragraph on page 1 as follows:

~~The present application~~ This is a divisional application of Application Serial No. 09/994,293 filed on November 26, 2002, which is a continuation-in-part of Application Serial No. 09/882,740 filed June 15, 2001 by Abdalla Aly Naem for Bipolar Transistor with a Silicon Germanium Base and an Ultra Small Self-Aligned Polysilicon Emitter and Method of Forming the Transistor.